	Туре	L #	Hits	Search Text	DBs
1	BRS	L1	62	violette near michael.in.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
2	BRS	L2	1768	438/257.ccls.	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
3	BRS	L3	78	2 and (select near line\$1)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
4	BRS	L4	5	2 and ((select near line\$1) near25 (nand))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Туре	L #	Hits	Search Text	DBs
5	BRS	L5	436	((select near line\$1) near25 (nand))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
6	BRS	L6	23	((select near line\$1) near25 (nand near string))	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
7	BRS	L7	2	((select near line\$1) near25 (nand)) near25 (dielectric or insulat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
8	BRS	L8	3	((select near line\$1 or sl) near25 (nand)) near25 (dielectric or insulat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Туре	L #	Hits	Search Text	DBs
9	BRS	L9	42	((select) near25 (nand)) near25 (dielectric or insulat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
10	BRS	L10	35	((conduct\$3 or poly\$4) near25 (nand)) near25 (dielectric or insulat\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
11	BRS	L11	28306	(third) near3 (conductiv\$3 or polysilicon)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
12	BRS	L12	37	(third) near3 (conductiv\$3 or polysilicon) near15 (nand)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Туре	L #	Hits	Search Text	DBs
13	BRS	L13	75		US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
14	BRS	L14	1921	(contact or hole\$1) near25 (nand)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
15	BRS	L15	67	1, ,	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B
16	BRS	L16	83	((opening or via or aperture) near25 (nand)) near15 (polysilicon or conductiv\$3)	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Туре	L #	Hits	Search Text	DBs
17	BRS	L17		((recess\$3) near25 (nand)) near15 (polysilicon or	US- PGPUB; USPAT; EPO; JPO; DERWEN T; IBM_TD B

	Ū	1	Document ID	Title
1		i .	US 20040026748 A1	Semiconductor device with source line and fabrication method thereof
2	Х		US 20040014286 A1	Method of forming a select line in a NAND type flash memory device
3	Х			Method of forming a select line in a NAND type flash memory device